Complementary Silicon Plastic Power Transistors

- . . . designed for use in general purpose amplifier and switching applications.
- Collector-Emitter Saturation Voltage -

VCE(sat) = 1.5 Vdc (Max) @ IC = 6.0 Adc

Collector–Emitter Sustaining Voltage —

VCEO(sus) = 60 Vdc (Min) — TIP41A, TIP42A = 80 Vdc (Min) — TIP41B, TIP42B = 100 Vdc (Min) — TIP41C, TIP42C

- High Current Gain Bandwidth Product
 fT = 3.0 MHz (Min) @ IC = 500 mAdc
- Compact TO-220 AB Package

*MAXIMUM RATINGS

Rating	Symbol	TIP41A TIP42A	TIP41B TIP42B	TIP41C TIP42C	Unit
Collector–Emitter Voltage	VCEO	60	80	100	Vdc
Collector-Base Voltage	VCB	60	80	100	Vdc
Emitter-Base Voltage	VEB	5.0		Vdc	
Collector Current — Continuous Peak	lC	6 10		Adc	
Base Current	ΙΒ	2.0		Adc	
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	65 0.52		Watts W/°C	
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	2.0 0.016		Watts W/°C	
Unclamped Inductive Load Energy (1)	E	62.5		mJ	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	_	-65 to +150	0	°C

THERMAL CHARACTERISTICS

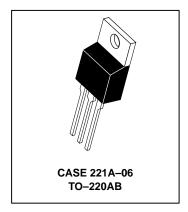
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	62.5	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.92	°C/W

⁽¹⁾ I $_{C}$ = 2.5 A, L = 20 mH, P.R.F. = 10 Hz, V $_{CC}$ = 10 V, R $_{BE}$ = 100 Ω_{\cdot}

TIP41A
TIP41B*
TIP41C*
PNP
TIP42A
TIP42B*
TIP42C*

*Motorola Preferred Device

6 AMPERE
POWER TRANSISTORS
COMPLEMENTARY
SILICON
60-80-100 VOLTS
65 WATTS



Preferred devices are Motorola recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (1) (I _C = 30 mAdc, I _B = 0)	TIP41A, TIP42A TIP41B, TIP42B TIP41C, TIP42C	VCEO(sus)	60 80 100	_ _ _	Vdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}$, $I_{B} = 0$) ($V_{CE} = 60 \text{ Vdc}$, $I_{B} = 0$)	TIP41A, TIP42A TIP41B, TIP41C TIP42B, TIP42C	ICEO		0.7 0.7 0.7	mAdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB} = 0) (V _{CE} = 80 Vdc, V _{EB} = 0) (V _{CE} = 100 Vdc, V _{EB} = 0)	TIP41A, TIP42A TIP41B, TIP42B TIP41C, TIP42C	ICES	111	400 400 400	μAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)		I _{EBO}	_	1.0	mAdc
ON CHARACTERISTICS (1)					
DC Current Gain ($I_C = 0.3$ Adc, $V_{CE} = 4.0$ Vdc) ($I_C = 3.0$ Adc, $V_{CE} = 4.0$ Vdc)		hFE	30 15	— 75	_
Collector-Emitter Saturation Voltage (I _C = 6.0 Adc, I _B = 600 mAdd	c)	VCE(sat)	_	1.5	Vdc
Base–Emitter On Voltage (I _C = 6.0 Adc, V _{CE} = 4.0 Vdc)		V _{BE} (on)	_	2.0	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (I _C = 500 mAdc, V _{CE} = 10 Vdc, f _{test} = 1.0 MHz)		fΤ	3.0	_	MHz
Small–Signal Current Gain (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1.0 kHz)		h _{fe}	20	_	_

⁽¹⁾ Pulse Test: Pulse Width $\leq 300 \, \mu s$, Duty Cycle $\leq 2.0\%$.

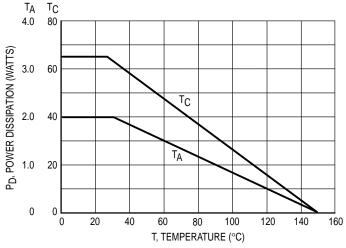
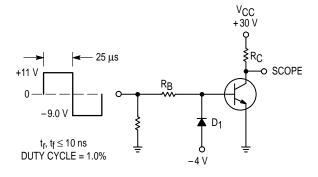


Figure 1. Power Derating



 R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS D_1 MUST BE FAST RECOVERY TYPE, e.g.: 1N5825 USED ABOVE $I_B \approx 100$ mA MSD6100 USED BELOW $I_B \approx 100$ mA

Figure 2. Switching Time Test Circuit

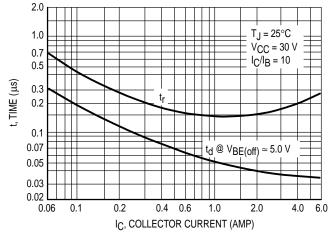


Figure 3. Turn-On Time

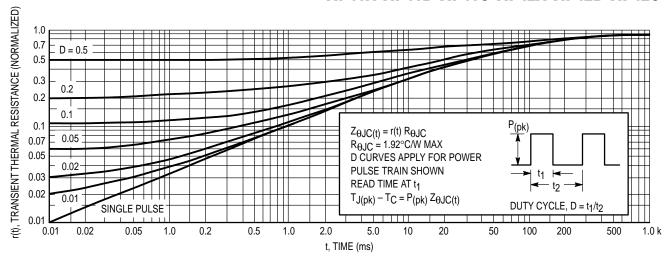


Figure 4. Thermal Response

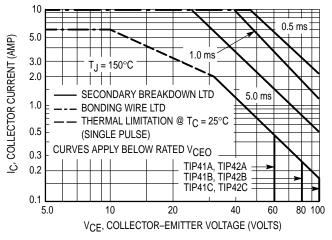


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_{\text{C}} - V_{\text{CE}}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

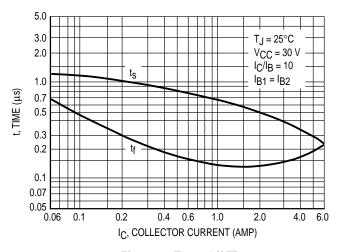


Figure 6. Turn-Off Time

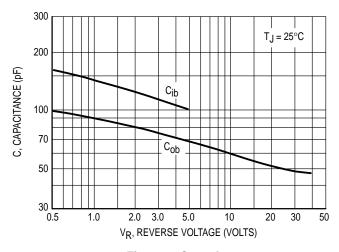


Figure 7. Capacitance

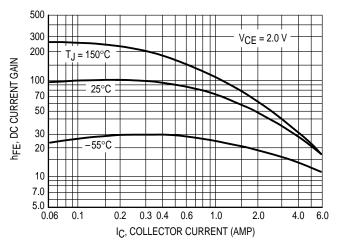


Figure 8. DC Current Gain

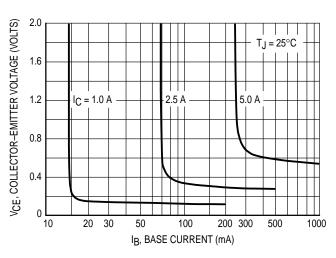


Figure 9. Collector Saturation Region

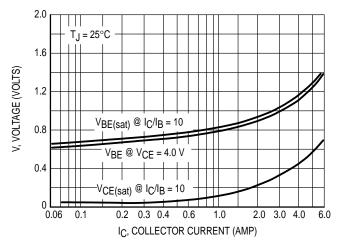


Figure 10. "On" Voltages

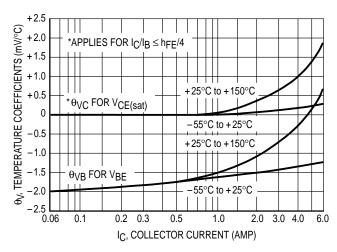


Figure 11. Temperature Coefficients

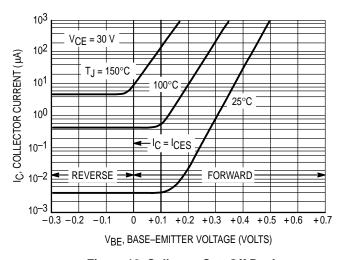


Figure 12. Collector Cut-Off Region

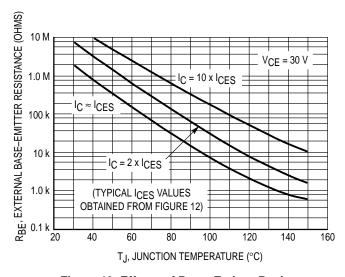
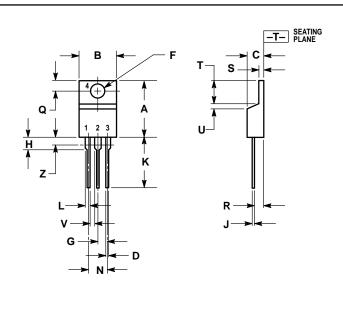


Figure 13. Effects of Base-Emitter Resistance

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.035	0.64	0.88	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.155	2.80	3.93	
J	0.018	0.025	0.46	0.64	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
T	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
٧	0.045		1.15		
Z		0.080		2.04	

- STYLE 1:
 PIN 1. BASE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR

CASE 221A-06 TO-220AB **ISSUE Y**

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and Employer.

How to reach us:

USA/EUROPE: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447

MFAX: RMFAX0@email.sps.mot.com – TOUCHTONE (602) 244–6609 INTERNET: http://Design-NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki, 6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298



